MUR860E

Rev.G Oct.-2018

/ Descriptions

TO-277

TO-277 Plastic package Ultrafast Recovery Diode.

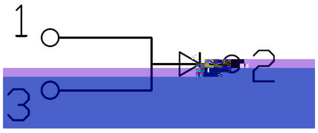
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability. HF Product.

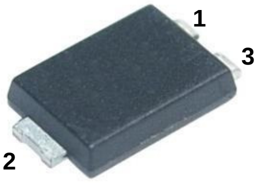
/ Applications

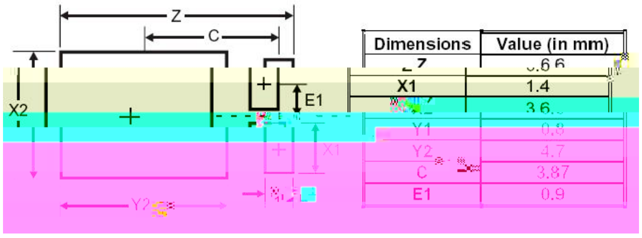
For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning





Dimensions	Value (in mm)
Z	[illegible]
X1	1.4
X2	3.6
Y1	0.8
Y2	4.7
C	3.87
E1	0.9

PIN1 Anode PIN 2 Cathode PIN 3 Anode

Suggested Pad layout

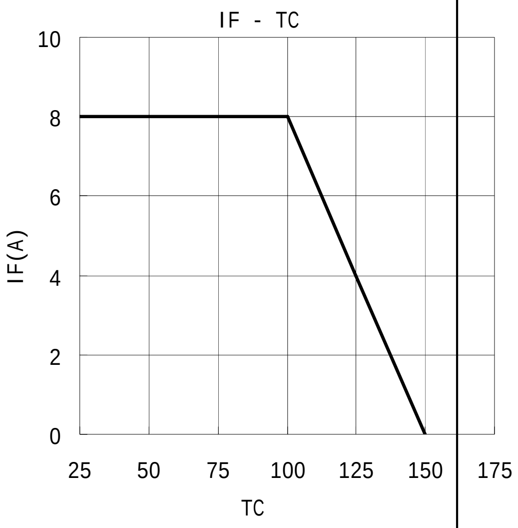
/ h_{FE} Classifications & Marking

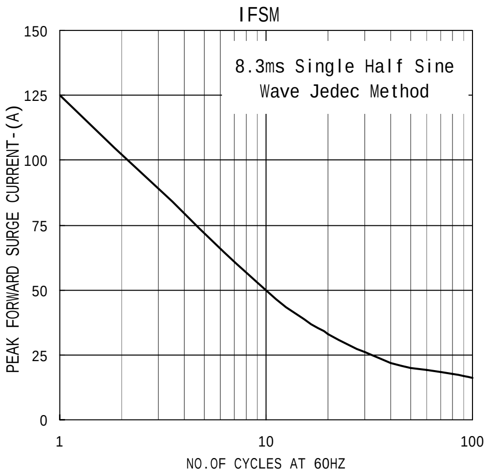
See Marking Instructions.

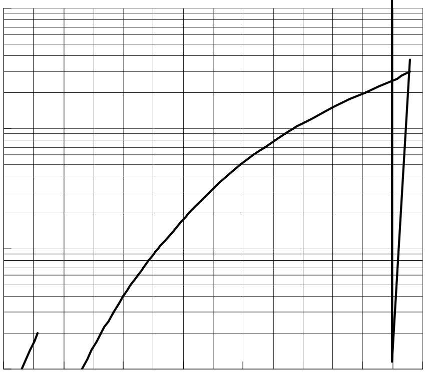
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	125	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Reverse Voltage	V_{BR}	I_R=100uA		600			V
Forward voltage	V_F	I_F=8A	Tc=25		1.4	1.7	V
		I_F=16A	Tc=25		1.7	2.1	V
		I_F=8A	Tc=125		1.4	1.7	V
Instantaneous Reverse Current	I_R Note 1	V_R=600V	Ta=25			5	uA
		V_R=480V	Ta=125			300	uA
		V_R=600V	Ta=125			500	uA

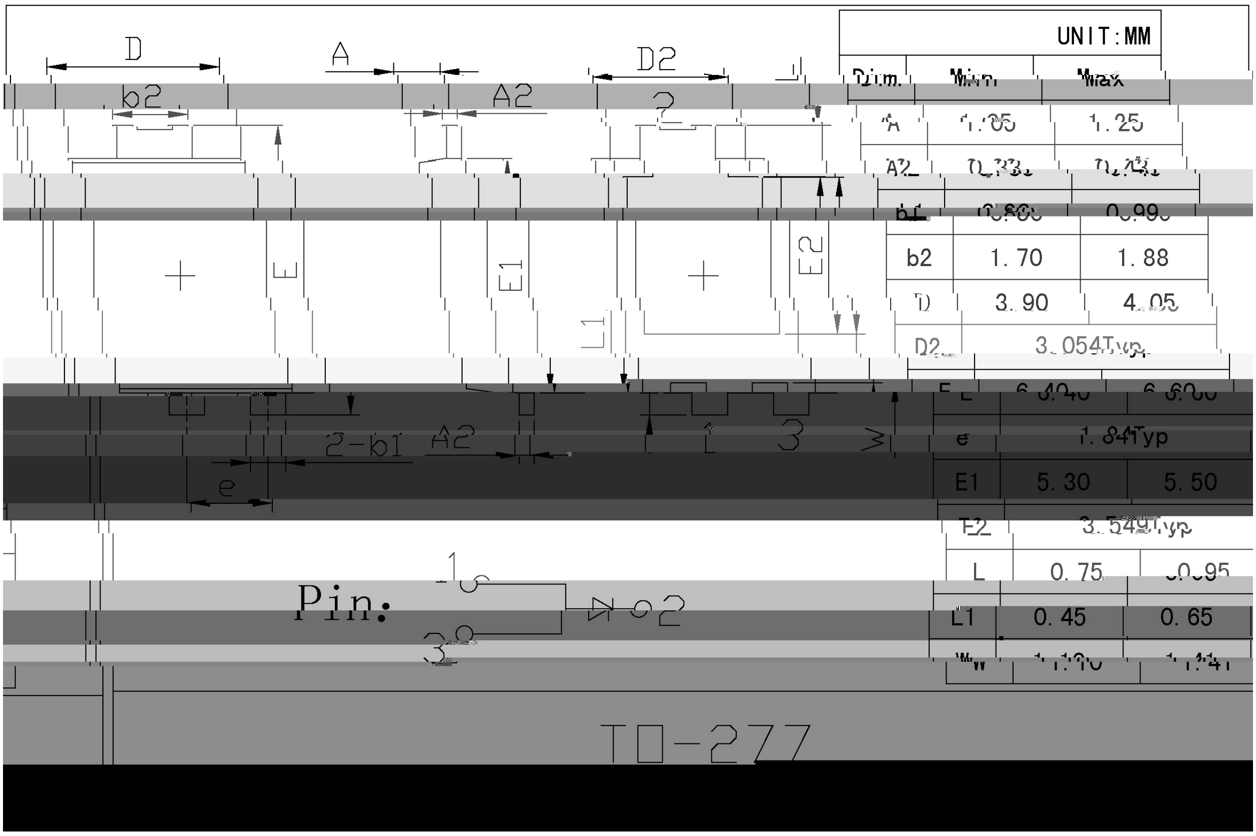
/ Electrical Characteristic Curve







/ Package Dimensions



UNIT:MM		
Dim.	Min	Max
A	1.05	1.25
A2	0.33	0.43
b1	0.80	0.99
b2	1.70	1.88
D	3.90	4.05
D2	3.054Typ	
E	6.40	6.60
e	1.84Typ	
E1	5.30	5.50
E2	3.549Typ	
L	0.75	0.95
L1	0.45	0.65
W	1.10	1.41

/ Marking Instructions

MUR860

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Note:

MUR860	Product Type.
****:	Lot No. Code, code change with Lot No.